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Photointerrupter Double Mold Type

RPI-128 **NEW**

Inquiries concerning our products

Data Sheet

[Product description]
 ROHM's optical sensors serve as eyes to monitor changes of any motions, and comply with customers' day-to-day diversifying requests.

Features

- Gap width 1.2mm
- Ultraminiature dip type

Product specifications

Absolute maximum ratings (Tc=25°C)		
Rated parameters	Standard value	Conditions
Input(LED)		
Forward current I _F (mA)	30	
Reverse voltage V _R (V)	5	
Power dissipation P _D (mW)	80	
Collector-Emitter voltage V _{CEO} (V)	30	
Output(Photo-toransistor)		
Emitter-Collector voltage V _{ECO} (V)	4.5	
Collector current I _C (mA)	30	
Power dissipation P _C (mW)	80	
Temperature Characteristics		
Operating temperature Topr(°C)	-25 to 85	
Storage temperature Tstg(°C)	-30 to 85	

Electro-optical characteristics (Ta=25°C)

Parameters	Value	Conditions
Input Characteristics		
Input Characteristics Forward voltage V _F (V)	1.35	I _F =5mA
Input Characteristics Reverse current I _R (μA)	10	V _R =5V
Output Characteristics		
Output Characteristics Dark current-Max. ICEO(μA)	0.1	V _{CE} =10V
Output Characteristics Peak sensitivity wavelength λP(nm)	800	
Transfer Characteristics		
Transfer Characteristics Collector current-Max. IC(mA)	1.00	V _{CE} =5V, I _F =5mA
Transfer Characteristics Collector-Emitter saturation voltage-Max. VCE(sat)(V)	0.4	I _F =20mA, I _C =0.1mA
Transfer Characteristics Response time tr·tf(μs)	10	V _{CC} =5V, I _F =20mA, R _L =100Ω
Infrared Light Emitting Diode		
Infrared Light Emitting Diode Cut-	-	I _F =50mA

Print out

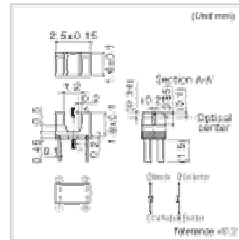
- Optical Sensors
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- Part No. explanation
- Notes on mounting
- Soldering conditions
- FAQ
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- RoHS directive compliance
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- What is a Optical Sensors?

Outline



Ultraminiature Type

Dimensions



* Click to enlarge.

off frequency F_C		* Non-coherent Infrared light emitting diode used.
Infrared Light Emitting Diode Peak light emitting wavelength λ_P (nm)	850	$I_F=50mA$ * Non-coherent Infrared light emitting diode used.
Phototransistor		
Phototransistor Response time t_{r-f} (μs)	10	$V_{CC}=5V, I_F=1mA, R_L=100\Omega$ * This product is not designed to be protected against electromagnetic wave.
Phototransistor Maximum sensitivity wavelength λ_P (nm)	800	-

*The contents described here are just outline for introduction.

Please obtain the specification sheets from us for thorough check before use.

Status Product

Part No.	Status *1	RoHS	Packing style	Package quantity	Samples *2	Sales
RPI-128	Active	Yes	Plastic bag	4000		Inquiry

*1 Active: Production or current type Preparation: Preliminary type Preview: Development type

*2 Available only as free rank.

Others

Please check the details on "[Product List](#)" for Others.

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